

High Speed SMD Switching Diode

FEATURES

- Fast switching device (trr<4.0ns)
- Surface device type mounting
- Matte Tin(Sn) terminal finish
- Pb free version and RoHS compliant

MECHANICAL DATA

- Case: Mini-MELF Package
- High temperature soldering guaranteed: 270°C/10s
- Polarity: Indicated by black cathode band
- Weight: 31mg (approximately)









Hermetically Sealed Glass

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (T _A =25°C unless otherwise noted)			
PARAMETER	SYMBOL	VALUE	UNIT
Power Dissipation	PD	500	mW
Repetitive Peak Reverse Voltage	V _{RRM}	75	V
Reverse Voltage	V _R	75	V
Peak Forward Surge Current (Note 1)	I _{FSM}	2	А
Non-Repetitive Peak Forward Current	I _{FM}	450	mA
Mean Forward Current	I _{F(AV)}	150	mA
Forward Continuous Current	l _F	150	mA
Repetitive Peak Forward Current	I _{FRM}	450	mA
Thermal Resistance (Junction to Ambient) (Note 2)	R _{θJA}	300	°C/W
Junction and Storage Temperature Range	T _J , T _{STG}	-65 to +175	°C

PARAMETER	2	SYMBOL	MIN	MAX	UNIT
Reverse Breakdown Voltage	I _R =100μΑ	V _(BR)	100	-	V
	Ι _R =5μΑ		75	-	
Forward Voltage			-	-	
LL4448, LL914B	I _F =5 mA	V	0.62	0.72	v
LL4148	I _F =50 mA	V _F	-	1	
LL4448, LL914B	I _F =100 mA	1 [-	1	
Deveree Leekege Current	V _R =20V	I	-	25	nA
Reverse Leakage Current	V _R =75V	I _R	-	5	μA
Junction Capacitance	V _R =0 f=1.0MHz	CJ	-	4	pF
Reverse Recovery Time	(Note 3)	t _{rr}	-	4	ns

Note 1: Test condition : 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)

Note 2: Valid provided that electrodes are kept at ambient temperature

Note 3: Reverse recovery test conditions : I_F = I_R =10mA, R_L =100 Ω , I_{RR} =1mA



RATINGS AND CHARACTERISTICS CURVES

(T_A=25°C unless otherwise noted)

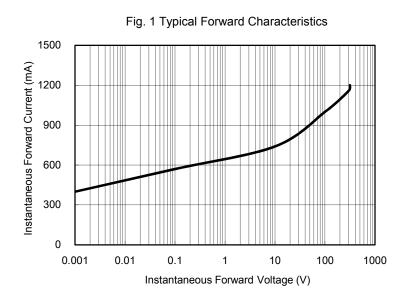


Fig. 3 Admissible Power Dissipation Curve

Ambient Temperature (°C)

Fig. 2 Reverse Current VS. Reverse Voltage

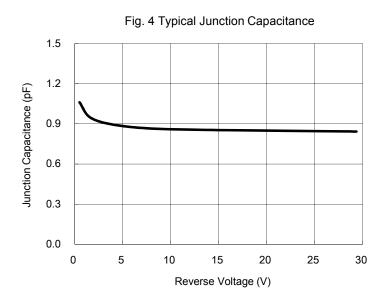


Fig. 5 Forward Resistance VS. Forward Current

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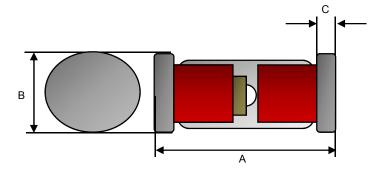
ORDER INFORMATION (EXAMPLE)

LL4148 LOG



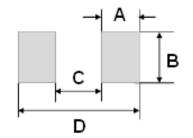
Green compound code Packing code Part no.

PACKAGE OUTLINE DIMENSION



DIM.	Unit (mm)		Unit (inch)	
DIN.	Min	Max	Min	Max
А	3.30	3.70	0.130	0.146
В	1.40	1.60	0.055	0.063
С	0.20	0.50	0.008	0.020

SUGGEST PAD LAYOUT



DIM.	Unit (mm)	Unit (inch)
DIN.	Тур.	Тур.
А	1.25	0.049
В	2.00	0.079
С	2.50	0.098
D	5.00	0.197



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